

Radiation	Type	Technology	Case
Infrared	DH	AlGaAs/GaAs	5 mm plastic lens

	Description High-power NIR-LED, housing without standoff leads Note: Special packages with standoff available on request
	Applications Remote control, safety equipment, automation

Maximum Ratings

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Forward current (DC)		I_F	100	mA
Peak forward current	($t_P \leq 50 \mu\text{s}$, $t_p/T = 1/2$)	I_{FM}	200	mA
Power dissipation		P_D	280	mW
Operating temperature range		T_{amb}	-20 to +100	°C
Storage temperature range		T_{stg}	-55 to +100	°C
Junction temperature		T_J	100	°C

Optical and Electrical Characteristics

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 100 \text{ mA}$	V_F		1,4	1,6	V
Reverse voltage	$I_R = 10 \mu\text{A}$	V_R	5			V
Radiant power	$I_F = 100 \text{ mA}$	Φ_e	25	35		mW
Radiant intensity	$I_F = 100 \text{ mA}$	I_e	50	70		mW/sr
Peak wavelength	$I_F = 100 \text{ mA}$	λ_P	925	940	955	nm
Spectral bandwidth at 50%	$I_F = 100 \text{ mA}$	$\Delta\lambda_{0.5}$		50		nm
Viewing angle	$I_F = 100 \text{ mA}$	φ		20		deg.
Switching time	$I_F = 100 \text{ mA}$	t_r, t_f		600		ns

Note: All measurements carried out on EPIGAP equipment

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.

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